

TS13002A

High Voltage NPN Transistor

Emitter



TO-92



Pin Definition:

- 1. Emitter
- 2. Collector
- 3. Base

PRODUCT SUMMARY

Block Diagram

BV _{CEO}	400V
BV _{CBO}	700V
Ic	0.3A
V _{CE(SAT)}	1.5V @ I _C / I _B = 200mA / 20mA

Features

- High Voltage
- High Speed Switching

Structure

- Silicon Triple Diffused Type
- NPN Silicon Transistor

Ordering Information

Part No.	Package	Packing
TS13002ACT B0G	TO-92	1Kpcs / Bulk
TS13002ACT A3G	TO-92	2Kpcs / Ammo

Note: "G" denote for Green Product

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Collector-Base Voltage	V _{CBO}	700V	V		
Collector-Emitter Voltage	,	$V_{\sf CEO}$	400V	V	
Emitter-Base Voltage		V_{EBO}	9	V	
Oallastan Ouwant	DC		0.3	•	
Collector Current	Pulse	Ic	0.5	A	
Collector Power Dissipation		P _D	0.6	W	
Operating Junction Temperature	TJ	+150	°C		
Operating Junction and Storage Tempera	T _{STG}	- 55 to +150	°C		

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Ambient Thermal Resistance	$R\Theta_{JA}$	122	°C/W



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	BV _{CBO}	700	1	1	V
Collector-Emitter Breakdown Voltage	$I_C = 10 \text{mA}, I_E = 0$	BV _{CEO}	400	-	1	V
Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	BV_{EBO}	9	-		V
Collector Cutoff Current	$V_{CB} = 700V, I_{E} = 0$	I _{CBO}		-	٦	uA
Emitter Cutoff Current	$V_{EB} = 7V, I_{C} = 0$	I _{EBO}		C	1	uA
	$I_{C} / I_{B} = 50 \text{mA} / 10 \text{mA}$	V _{CE(SAT)1}		0.2	0.4	
Collector-Emitter Saturation Voltage	$I_C / I_B = 100 \text{mA} / 10 \text{mA}$	V _{CE(SAT)2}		0.45	1	V
	$I_C / I_B = 200 \text{mA} / 20 \text{mA}$	V _{CE(SAT)3}		1	1.5	
Base-Emitter Saturation Voltage	$I_C / I_B = 50 \text{mA} / 10 \text{mA}$	V _{BE(SAT)1}			1	V
base-Emitter Saturation voltage	$I_{C} / I_{B} = 100 \text{mA} / 10 \text{mA}$	V _{BE(SAT)2}	7		1.2	V
	$V_{CE} = 10V, I_{C} = 10mA$	h _{FE} 1	15		40	
DC Current Gain	$V_{CE} = 10V, I_{C} = 100mA$	h _{FE} 2	25		40	
	$V_{CE} = 10V, I_{C} = 280mA$	h _{FE} 3	12		24	
Dynamic		*				
Frequency	$V_{CE} = 10V, I_{C} = 0.1A$	f _T	4			MHz
Output Capacitance	$V_{CB} = 10V, f = 0.1MHz$	Cob		21		pF
Resistive Load Switching Time (Ratio	ngs)					
Rise Time	$V_{CC} = 125V$, $I_C = 100mA$,	t _r		1.1	-	uS
Storage Time	$I_{B1} = I_{B2} = 20\text{mA},$ $I_{a} = 25\text{uS}$	t _{STG}		2	4	uS
Fall Time	Duty Cycle ≤1%	t _f		0.2	0.7	uS

Note : pulse test: pulse width ≤ 5mS, duty cycle ≤10%





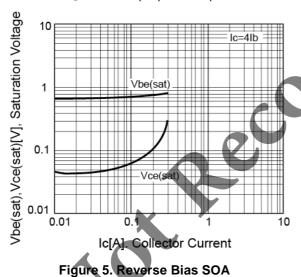
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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics 600 Ic[mA], Collector Current lb=90mA Ib=80mA 500 Ib=70mA Ib=60mA 400 30mA 300 200 Ib=10mA 100 lb=1mA 0 Vce[V], Collector-Emitter Voltage

Figure 3. V_{CE(SAT)} v.s. V_{BE(SAT)}



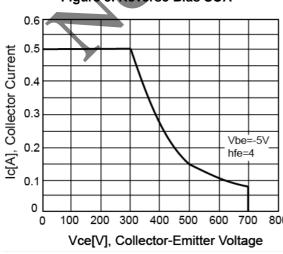


Figure 2. DC Current Gain

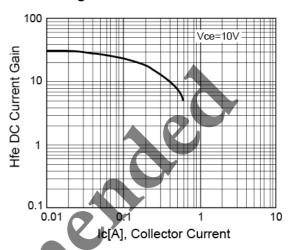


Figure 4. Power Derating

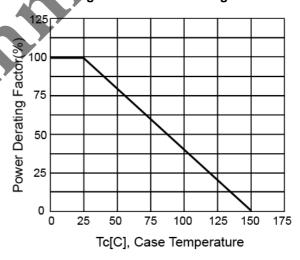
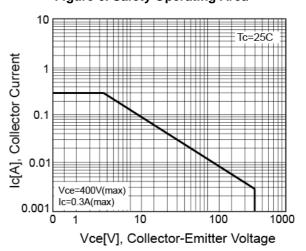
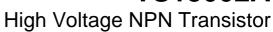


Figure 6. Safety Operating Area

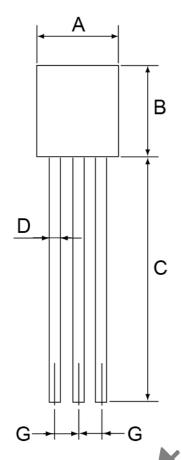






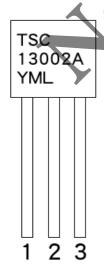


TO-92 Mechanical Drawing



TO-92 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.30	4.70	0.169	0.185		
В	4.30	4,70	0.169	0.185		
С	13.53	(typ)	0.532 (typ)			
D	0.39	0.49	0.015	0.019		
Е	1.18	1.28	0.046	0.050		
F	3.30	3.70	0.130	0.146		
G	1.27	1.31	0.050	0.051		
H	0.33	0.43	0.013	0.017		





Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



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